

Data sheet	
status	Product specification
date of issue	June 1990

FCB61C65(L/LL)

8 K x 8 Fast CMOS low-power static RAM

FOR DETAILED INFORMATION SEE RELEVANT DATA BOOK OR DATA SHEET

FEATURES

- Operating supply voltage
5 V $\pm$ 10%
- Inputs and outputs ESD protected
- Automatic power-down after a completed read access
- Access time: 55 ns and 70 ns
- Low current consumption:

active	70 mA max.
standby (TTL)	3 mA max.
standby (CMOS)	100 μ A max.
	(L-version)
standby (CMOS)	1 μ A max.
	(LL-version)
- Suitable for battery back-up operation: (FCB61C65L/LL only)

data retention voltage	2 V min.
data retention current	50 μ A max.
	(L-version)
data retention current	1 μ A max.
	(LL-version)
- Latched data outputs giving stable data between consecutive accesses
- Easy memory expansion
- Common data I/O interface
- All inputs and outputs TTL and CMOS compatible
- All inputs have a Schmitt trigger switching action
- Three-state outputs
- Operating temperature 0 °C to +70 °C

GENERAL DESCRIPTION

The FCB61C65(L/LL) is a 65536-bit fast, low-power, static random access memory organized as 8192 words of 8 bits each.

The chip enable inputs $\overline{CE}1$ and $CE2$ are available for memory expansion and to control the low-power/standby mode.

The device operates from a 5 V power supply and has an access time of 55 ns and 70 ns.

The FCB61C65(L/LL) is ideally suited for memory applications where fast access time, low power and ease of use are required.

The FCB61C65(L/LL) is a CMOS device which uses a 6 transistor memory cell.

The IC is fabricated in a CMOS double-metal single-poly process using ion-implanted silicon gate technology.

ORDERING AND PACKAGE INFORMATION

EXTENDED TYPE NUMBER	PACKAGE			
	PINS	PIN POSITION	MATERIAL	CODE
FCB61C65 (L/LL)-XXP	28	DIL (600 mil)	plastic	SOT117
FCB61C65 (L/LL)-XXT	28	SO28XL (330 mil)	plastic	SOT213

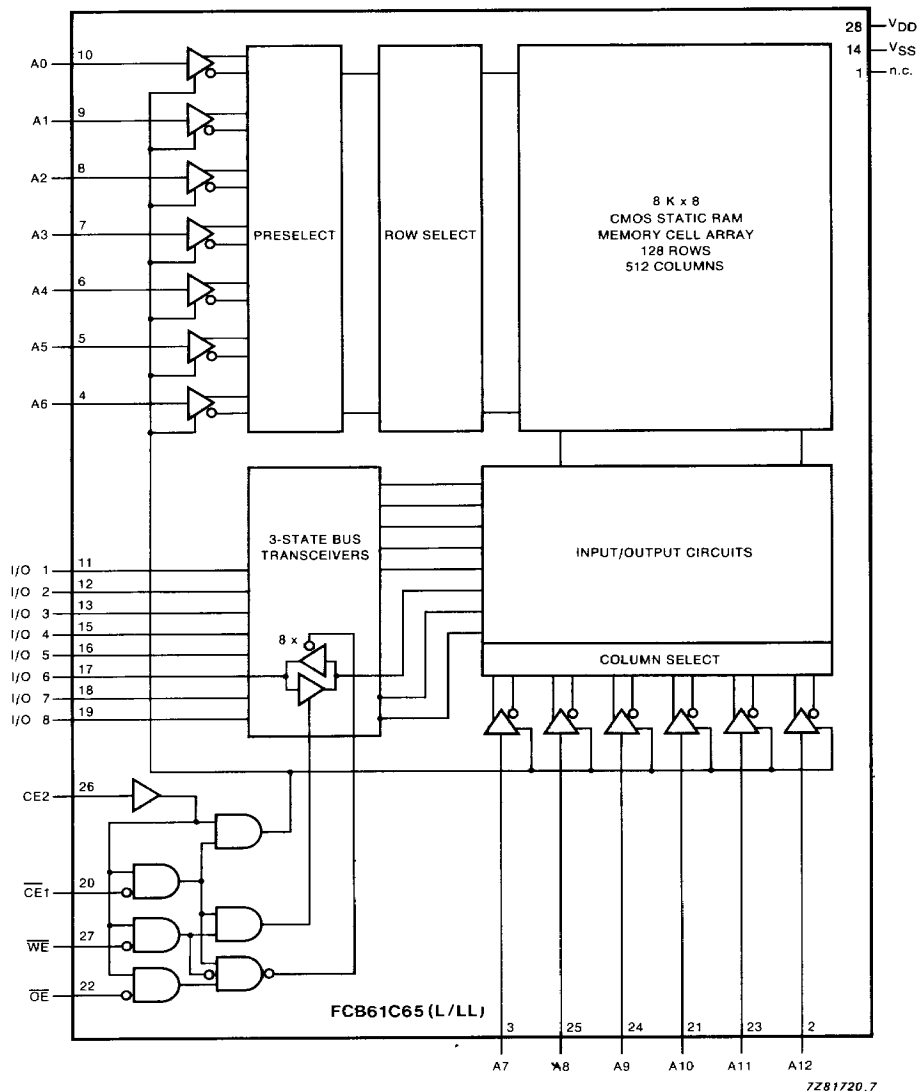
8 K x 8 Fast CMOS low-power static RAM**FCB61C65(L/LL)**

Fig.1 Block diagram.

8 K x 8 Fast CMOS low-power static RAM

FCB61C65(L/LL)

TRUTH TABLE

CE1	CE2	OE	WE	MODE	I _{DD}	I/O PIN	REF. CYCLE
H	X	X	X	not selected	I _{SB} *	HIGH Z	
X	L	-X	X	not selected	I _{SB} *	HIGH Z	
L	H	L	H	read	I _{DD} /I _{DD1} *	D OUT	read
L	H	H	L	write	I _{DD}	D IN	write
L	H	L	L	write	I _{DD}	D IN	write
L	H	H	H	ready-read	I _{DD} /I _{DD1} *	HIGH Z	

* Including L/LL versions if input levels are CMOS.

PINNING

SYMBOL	PIN	DESCRIPTION
n.c.	1	not connected
A12	2	address input
A7 to A0	3 to 10	address inputs
I/O 1 to I/O 3	11 to 13	data inputs/outputs
V _{SS}	14	ground
I/O 4 to I/O 8	15 to 19	data inputs/outputs
CE1	20	chip enable 1
A10	21	address input
OE	22	output enable
A11, A9, A8	23 to 25	address inputs
CE2	26	chip enable 2
WE	27	write enable
V _{DD}	28	+5 V supply

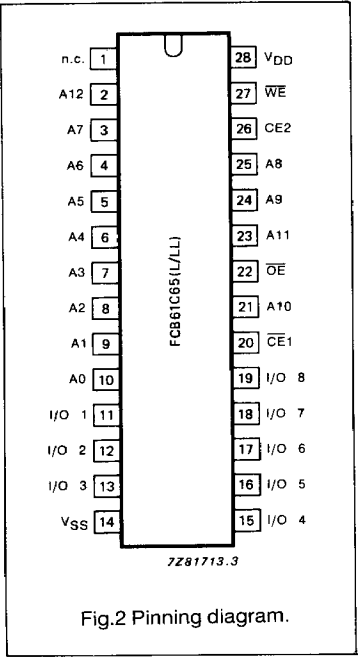


Fig.2 Pinning diagram.

8 K x 8 Fast CMOS low-power static RAM

FCB61C65(L/LL)

DC CHARACTERISTICS

V_{DD} = 5 V ± 10%; T_{amb} = 0 to 70 °C. Typical readings taken at V_{DD} = 5 V; T_{amb} = 25 °C. All voltages are referenced to V_{SS} (0 V) unless otherwise specified. DC characteristics are valid after thermal equilibrium has been established.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{LI}	input leakage current	V _I = V _{SS} to V _{DD}	-1	-	1	µA
I _{LO}	output leakage current	$\overline{CE}1$ or $\overline{OE}$ = V _{IH} or CE2 = V _{IL} ; V _{I/O} = V _{SS} to V _{DD}	-1	-	1	µA
I _{DD}	average operating current	cycle time 55 ns; 100% duty factor; note 1 I _{I/O} = 0 mA	-	40	70	mA
I _{DD}	average operating current	cycle time 70 ns; 100% duty factor; note 1 I _{I/O} = 0 mA	-	35	60	mA
I _{DD1}	DC operating current	$\overline{WE}$ = V _{IH} ; I _{I/O} = 0 mA; f = 0 Hz $\overline{WE}$ = CMOSH; V _I = CMOS; note 2	-	3	6	mA
I _{DDL}	FCB61C65L only		-	2	100	µA
I _{DDL}	FCB61C65LL only		-	0.05	1.0	µA
I _{SB}	standby current	$\overline{CE}1$ = V _{IH} or CE2 = V _{IL} $\overline{CE}1$ = CMOSH and CE2 = CMOS or CE2 = CMOSL	-	1.5	3.0	mA
I _{SBL}	FCB61C65L only		-	2	100	µA
I _{SBL}	FCB61C65LL only		-	0.05	1.0	µA
V _{OL}	output voltage LOW	I _{OL} = 4 mA	-	-	0.4	V
V _{OL}	output voltage LOW	I _{OL} = 20 µA	-	-	0.2	V
V _{OH}	output voltage HIGH	I _{OH} = -1 mA	2.4	-	-	V
V _{OH}	output voltage HIGH	I _{OH} = -20 µA	V _{DD} -0.2	-	-	V

Notes to the DC characteristics

1. I_{DD} ≤ 50 mA at a cycle time of 100 ns and ≤ 45 mA at a cycle time of 120 ns.
2. CMOS = CMOSH: V_{DD} - 0.2 V ≤ level ≤ V_{DD} + 0.2 V or
CMOSL: -0.2 V ≤ level ≤ +0.2 V.

CAPACITANCES

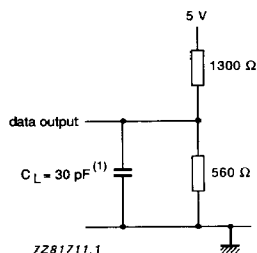
f = 1 MHz; T_{amb} = 25 °C (parameters in this table are sampled and not 100% tested).

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
C _I	input capacitance	V _I = 0 V	8	pF
C _I	$\overline{CE}1$, CE2, $\overline{WE}$, $\overline{OE}$ all other inputs	V _I = 0 V	7	pF
C _{I/O}	input/output capacitance	V _{I/O} = 0 V	8	pF

8 K x 8 Fast CMOS low-power static RAM**FCB61C65(L/LL)****TIMING CHARACTERISTICS**

$V_{DD} = 5\text{ V} \pm 10\%$; $T_{amb} = 0\text{ to }70\text{ }^{\circ}\text{C}$; inputs pulse levels = 0.4 to 2.4 V; input rise and fall times = 5 ns; input and output timing reference levels = 1.5 V and output loading as in Figure 3; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	55 TYPE		70 TYPE		UNIT
			MIN.	MAX.	MIN.	MAX.	
Read cycle							
t _{RC}	read cycle time		55	-	70	-	ns
t _{AA}	address access time		-	55	-	70	ns
t _{ACE}	chip enable access time		-	55	-	70	ns
t _{OE}	output enable access time		-	30	-	35	ns
t _{CLZ}	chip enable to output LOW Z	note 6	5	-	5	-	ns
t _{OLZ}	output enable to output LOW Z	note 6	5	-	5	-	ns
t _{CHZ}	chip disable to output HIGH Z	note 6	-	30	-	30	ns
t _{OHZ}	output disable to output HIGH Z	note 6	-	30	-	30	ns
t _{OH}	output hold time		10	-	10	-	ns
Write cycle							
t _{WC}	write cycle time		55	-	70	-	ns
t _{CW}	chip enable to end of write	note 11	50	-	65	-	ns
t _{AW}	address valid to end of write		50	-	65	-	ns
t _{AS}	address set up time		0	-	0	-	ns
t _{WP}	write pulse width	note 9	30	-	35	-	ns
t _{WR}	write recovery time	note 10	0	-	0	-	ns
t _{WHZ}	write enable to output HIGH Z	note 16	-	20	-	25	ns
t _{DW}	data to write time overlap		25	-	30	-	ns
t _{DH}	data hold from write time		5	-	5	-	ns
t _{OW}	end of write to output LOW Z	note 16	5	-	5	-	ns

Output load

(1) $C_L = 5\text{ pF}$ for t_{CLZ} , t_{CHZ} , t_{WHZ} , t_{OLZ} , t_{OHZ} and t_{OW} .

Fig.3 Output load.

8 K x 8 Fast CMOS low-power static RAM

FCB61C65(L/LL)

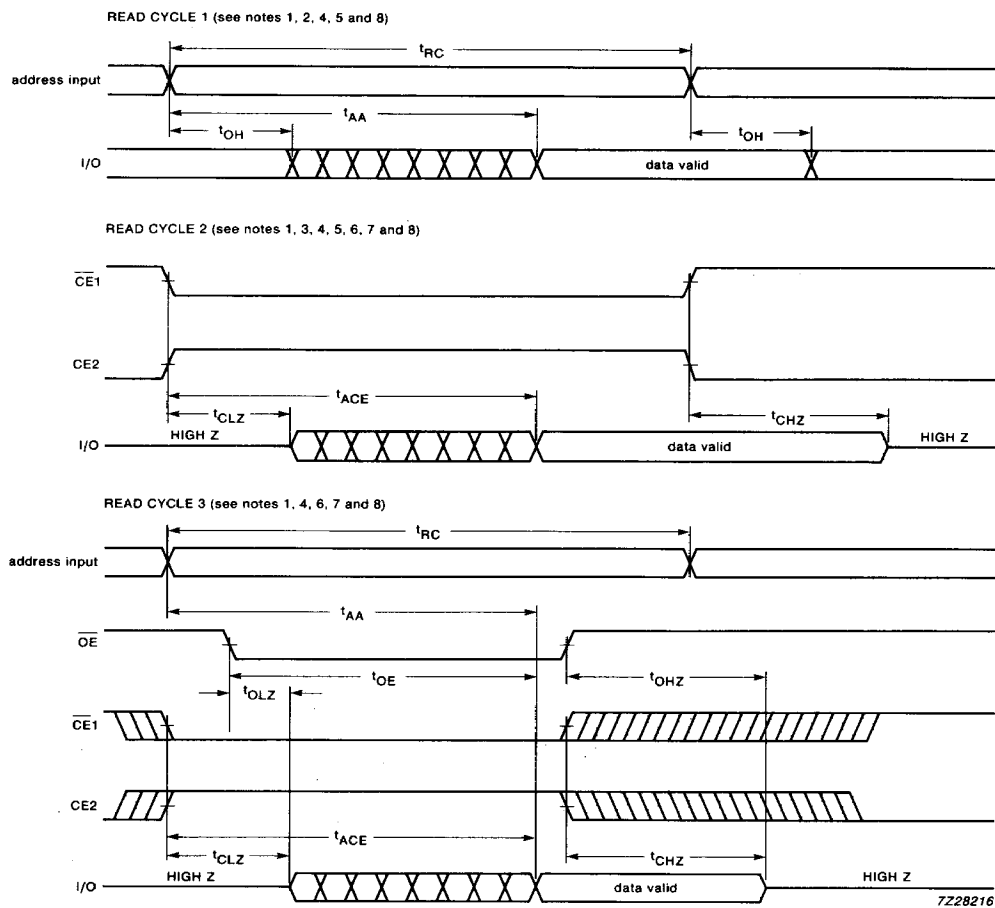


Fig.4 Read cycle timing.

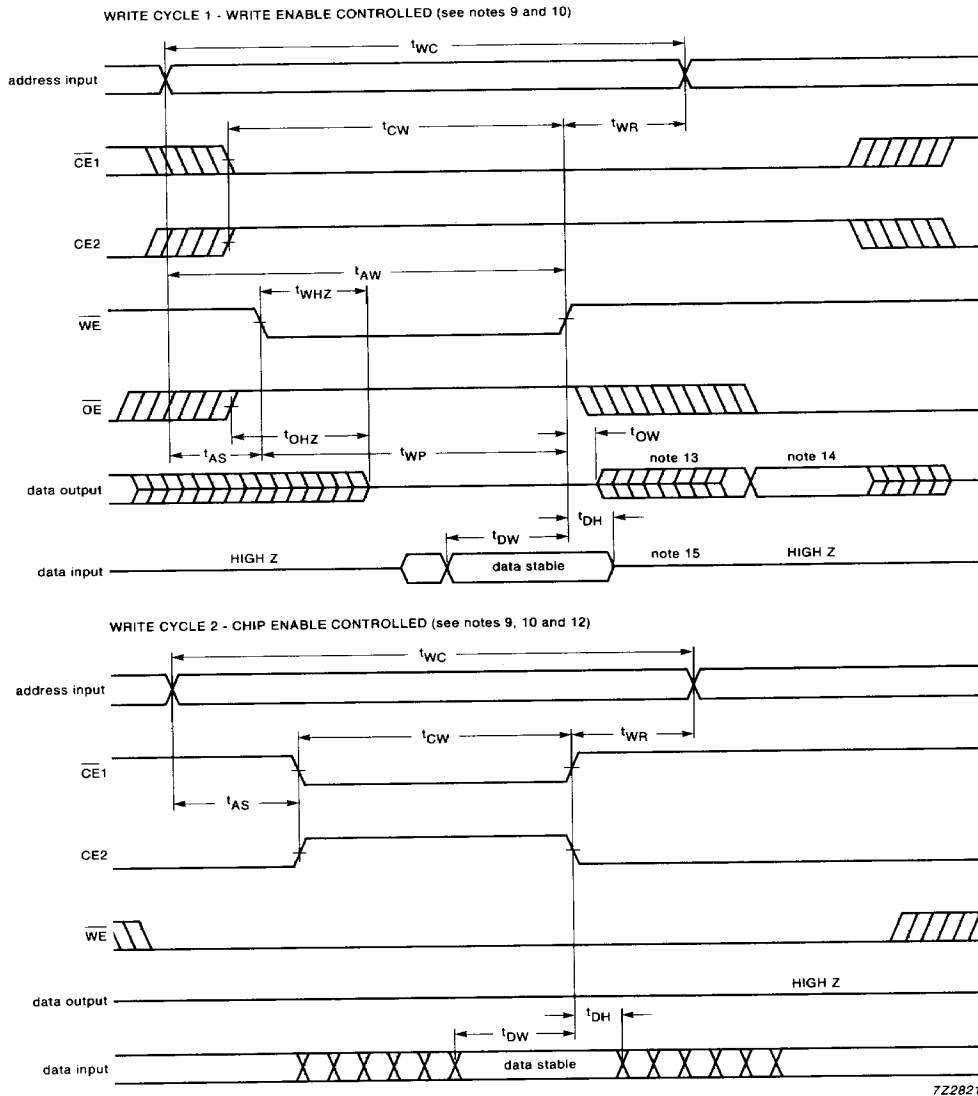
8 K x 8 Fast CMOS low-power static RAM**FCB61C65(L/LL)**

Fig.5 Write cycle timing.

8 K x 8 Fast CMOS low-power static RAM**FCB61C65(L/LL)****Notes to the timing characteristics****Read cycle** (see Fig.4)

1. $\overline{WE}$ is HIGH for read cycle.
2. Device is continuously selected, $\overline{CE1}$ is LOW and CE2 is HIGH.
3. Address is valid prior to or coincident with $\overline{CE1}$ LOW or CE2 HIGH transition.
4. When $\overline{CE1}$ is LOW and CE2 HIGH, the address inputs may not be floating.
5. $\overline{OE}$ is LOW.
6. $C_L = 5$ pF for t_{CLZ} , t_{CHZ} , t_{OLZ} , output transition measured at ± 200 mV from preceding steady state. These parameters are sampled and not 100% tested.
7. t_{CLZ} and t_{ACE} are measured from the last $\overline{CE1}$ going LOW or CE2 going HIGH. t_{CHZ} is measured from the first of $\overline{CE1}$ going HIGH or CE2 going LOW.
8. If D OUT in two consecutive read cycles is the same, D OUT remains stable.

Write cycle (see Fig.5)

9. A write occurs during an overlap of LOW $\overline{CE1}$, a HIGH CE2 and a LOW $\overline{WE}$.
10. t_{WR} is measured from the earlier of CE2 going to LOW or $\overline{CE1}$ or $\overline{WE}$ going HIGH at the end of a write cycle.
11. If the $\overline{CE1}$ /CE2 transition occurs simultaneously to or after the $\overline{WE}$ LOW transition the outputs remain in a high impedance state.
12. $\overline{OE}$ is continuously LOW.
13. D OUT is in the same phase as the write data of this write cycle.
14. D OUT is the read data of the next address.
15. If $\overline{CE1}$ is LOW (CE2 is HIGH) and I/O pins are in the output state during this period then input data signals of opposite phase to the outputs must not be applied.
16. $C_L = 5$ pF for t_{WHZ} and t_{OW} , measured at ± 200 mV from steady state. These parameters are sampled and not 100% tested.

8 K x 8 Fast CMOS low-power static RAM

FCB61C65(L/LL)

DATA RETENTION CHARACTERISTICS FOR LOW POWER/STANDBY MODE

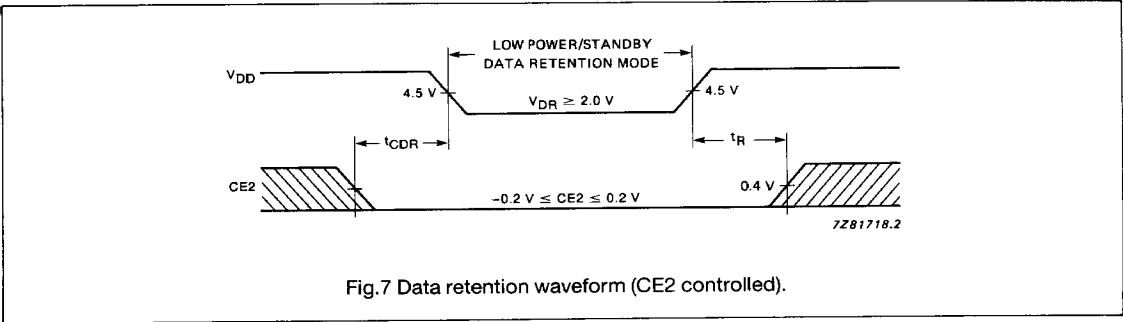
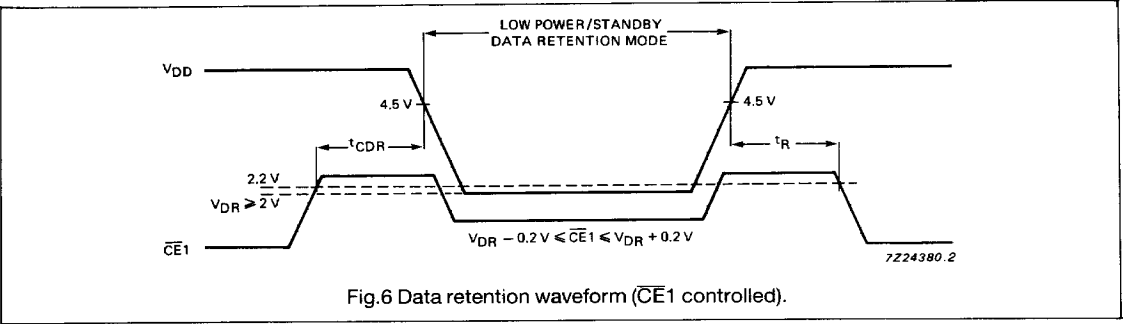
(FCB61C65L/LL only)

T_{amb} = 0 to +70 °C; I_{DRL}/LL measurements are valid after thermal equilibrium has been established.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supply						
V _{DR}	supply voltage for data retention	$\overline{CE}1 = \text{CMOSH}$ or $CE2 = \text{CMOSL}$ with other $V_i = \text{CMOS}$; note 1	2.0	-	5.5	V
I _{DRL} I _{DRL} LL	supply current during data retention FCB61C65L only FCB61C65LL only	V _{DR} = 3 V; CE2 = CMOSL; other $V_i = \text{CMOS}$ or $\overline{CE}1 = \text{CMOSH}$; other $V_i = \text{CMOS}$	- -	2 0.05	50 1	μA μA
Timing						
t _{CDR}	chip disable to data retention time		0	-	-	ns
t _R	recovery time to fully active	note 2	t _{RC}	-	-	ns

Notes to the data retention characteristics

- 1. CMOS = CMOSH: $V_{\text{DR}} - 0.2 \text{ V} \leq \text{level} \leq V_{\text{DR}} + 0.2 \text{ V}$ or
CMOSL: $-0.2 \text{ V} \leq \text{level} \leq +0.2 \text{ V}$.
- 2. t_{RC} = read cycle time.



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Data sheet	
status	Product specification
date of issue	August 1990

FCF61C65(L/LL)

8 K x 8 Fast CMOS low-power static RAM for extended temperature range

FOR DETAILED INFORMATION SEE RELEVANT DATA BOOK OR DATA SHEET

FEATURES

- Operating supply voltage
5 V $\pm$ 10%
- Inputs and outputs ESD protected
- Automatic power-down after a completed read access
- Access time: 85 ns
- Low current consumption:

active	60 mA max.
standby (TTL)	3 mA max.
standby (CMOS)	200 μ A max.
	(L-version)
standby (CMOS)	4 μ A max.
	(LL-version)
- Suitable for battery back-up operation: (FCF61C65L/LL only)

data retention voltage	2 V min.
data retention current	100 μ A max.
	(L-version)
data retention current	4 μ A max.
	(LL-version)
- Latched data outputs giving stable data between consecutive accesses
- Easy memory expansion
- Common data I/O interface
- All input and outputs TTL and CMOS compatible
- All inputs have a Schmitt trigger switching action
- Three-state outputs
- Operating temperature -40°C to $+85^{\circ}\text{C}$

GENERAL DESCRIPTION

The FCF61C65(L/LL) is a 65536-bit, fast, low-power, static random access memory organized as 8192 words of 8 bits each.

The chip enable inputs $\overline{\text{CE}}1$ and $\overline{\text{CE}}2$ are available for memory expansion and to control the lower-power/standby mode.

The device operates from a 5 V power supply and has an access time of 85 ns.

The FCF61C65(L/LL) is ideally suited for memory applications for the extended temperature range of -40 to $+85^{\circ}\text{C}$ where fast access time, low power and ease of use are required.

The FCF61C65(L/LL) is a full CMOS device using a 6 transistor memory cell.

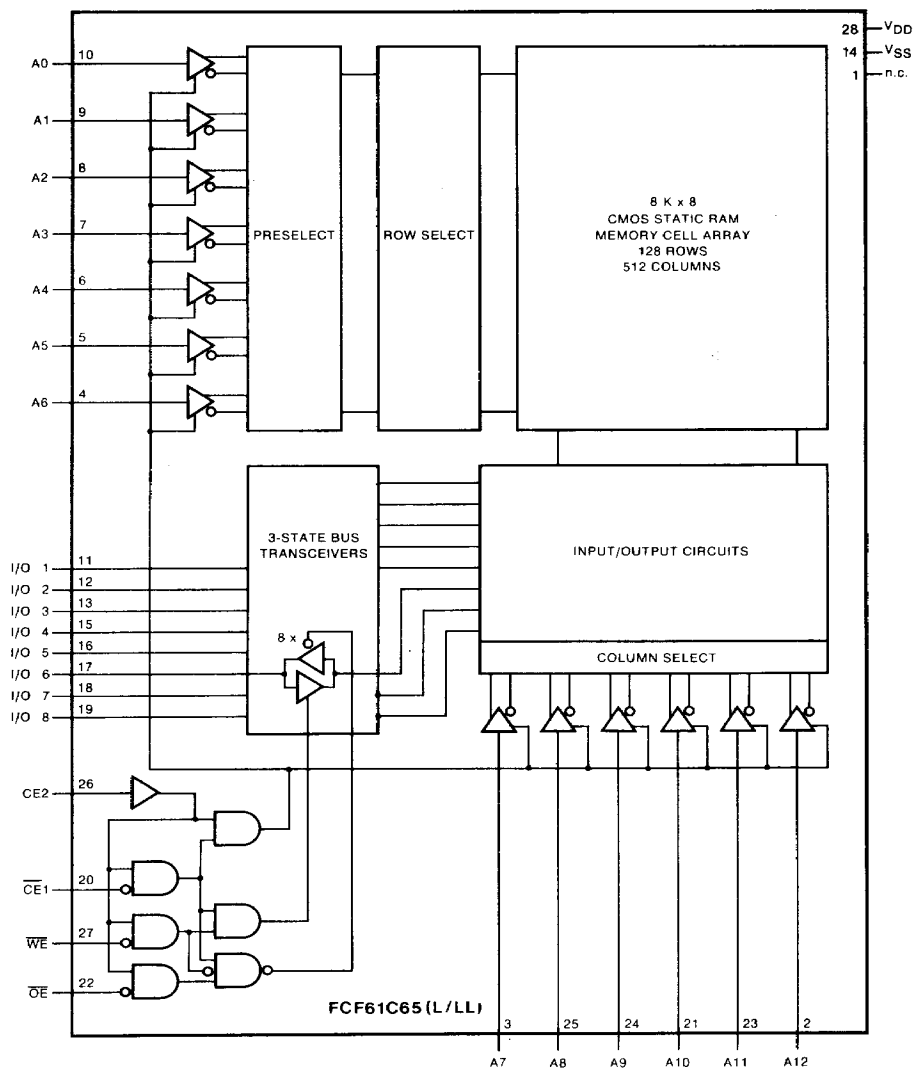
The IC is fabricated in a CMOS double-metal single-poly process using ion-implanted silicon gate technology.

ORDERING AND PACKAGE INFORMATION

EXTENDED TYPE NUMBER	PACKAGE			
	PINS	PIN POSITION	MATERIAL	CODE
FCF61C65 (L/LL)-85T	28	SO28XL(330mil)	plastic	SOT213

8 K x 8 Fast CMOS low-power static RAM for extended temperature range

FCF61C65(L/LL)



7Z26566

Fig.1 Block diagram.

8 K x 8 Fast CMOS low-power static RAM for extended temperature range

FCF61C65(L/LL)

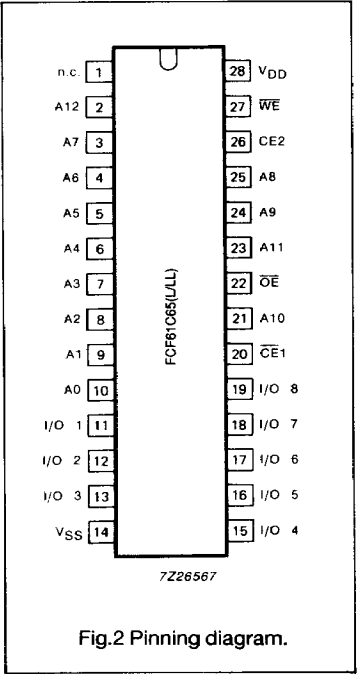
TRUTH TABLE

CE1	CE2	OE	WE	MODE	I _{DD}	I/O PIN	REF. CYCLE
H	X	X	X	not selected	I _{SB} *	HIGH Z	
X	L	X	X	not selected	I _{SB} *	HIGH Z	
L	H	L	H	read	I _{DD} /I _{DD1} *	D OUT	read
L	H	H	L	write	I _{DD}	D IN	write
L	H	L	L	write	I _{DD}	D IN	write
L	H	H	H	ready-read	I _{DD} /I _{DD1} *	HIGH Z	

* Including L/LL versions if input levels are CMOS.

PINNING

SYMBOL	PIN	DESCRIPTION
n.c.	1	not connected
A12	2	address input
A7 to A0	3 to 10	address inputs
I/O 1 to I/O 3	11 to 13	data inputs/outputs
V _{SS}	14	ground
I/O 4 to I/O 8	15 to 19	data inputs/outputs
CE1	20	chip enable 1
A10	21	address input
OE	22	output enable
A11, A9, A8	23 to 25	address inputs
CE2	26	chip enable 2
WE	27	write enable
V _{DD}	28	+5 V supply



8 K x 8 Fast CMOS low-power static RAM for extended temperature range

FCF61C65(L/LL)

DC CHARACTERISTICS

$V_{DD} = 5\text{ V} \pm 10\%$; $T_{\text{amb}} = -40\text{ to }+85\text{ }^{\circ}\text{C}$. Typical readings taken at $V_{DD} = 5\text{ V}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$. All voltages are referenced to V_{SS} (0 V) unless otherwise specified. DC characteristics are valid after thermal equilibrium has been established.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{LI}	input leakage current	$V_I = V_{SS}\text{ to }V_{DD}$	-2	-	2	μA
I_{LO}	output leakage current	$\overline{CE}1\text{ or }OE = V_{IH}\text{ or }CE2 = V_{IL};$ $V_{I/O} = V_{SS}\text{ to }V_{DD}$	-2	-	2	μA
I_{DD}	average operating current	cycle time 85 ns; 100% duty factor; note 1 $I_{I/O} = 0\text{ mA}$	-	35	60	mA
I_{DD1}	DC operating current	$\overline{WE} = V_{IH}; I_{I/O} = 0\text{ mA}; f = 0\text{ Hz}$	-	3	10	mA
I_{DDL}	FCF61C65L only FCF61C65LL only	$\overline{WE} = \text{CMOSH}; V_I = \text{CMOS};$ notes 2 and 3	-	2	200	μA
I_{DDL}			-	0.05	4	μA
I_{SB}	standby current	$\overline{CE}1 = V_{IH}\text{ or }CE2 = V_{IL}$	-	1.5	3.0	mA
I_{SBL}	FCF61C65L only FCF61C65LL only	$\overline{CE}1 = \text{CMOSH and }CE2 = \text{CMOS}$ or $CE2 = \text{CMOSL};$ notes 2 and 3	-	2	200	μA
I_{SBL}			-	0.05	4	μA
V_{OL}	output voltage LOW	$I_{OL} = 4\text{ mA}$	-	-	0.4	V
V_{OL}	output voltage LOW	$I_{OL} = 20\text{ }\mu\text{A}$	-	-	0.2	V
V_{OH}	output voltage HIGH	$I_{OH} = -1\text{ mA}$	2.4	-	-	V
V_{OH}	output voltage HIGH	$I_{OH} = -20\text{ }\mu\text{A}$	$V_{DD}-0.2$	-	-	V

Notes to the DC characteristics

- $I_{DD} \leq 55\text{ mA}$ at a cycle time of 100 ns and $\leq 50\text{ mA}$ at a cycle time of 120 ns.
- CMOS = CMOSH: $V_{DD} - 0.2\text{ V} \leq \text{level} \leq V_{DD} + 0.2\text{ V}$ or
CMOSL: $-0.2\text{ V} \leq \text{level} \leq +0.2\text{ V}$.
- At $T_{\text{amb}} = 70\text{ }^{\circ}\text{C}$: $I_{SBL}/I_{DDL} \leq 100\text{ }\mu\text{A max.}$ and
 $I_{SBL}/I_{DDL} \leq 1\text{ }\mu\text{A max.}$

CAPACITANCES

$f = 1\text{ MHz}$; $T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$ (parameters in this table are sampled and not 100% tested).

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
C_i	input capacitance $\overline{CE}1, CE2, \overline{WE}, OE$	$V_I = 0\text{ V}$	8	pF
C_i		$V_I = 0\text{ V}$	7	pF
$C_{I/O}$	input/output capacitance	$V_{I/O} = 0\text{ V}$	8	pF

8 K x 8 Fast CMOS low-power static RAM for
extended temperature range

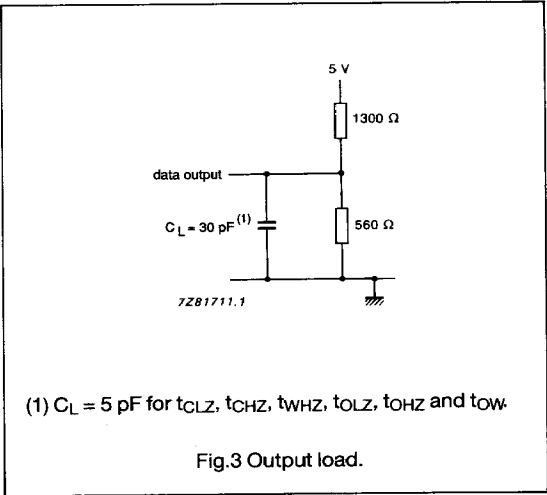
FCF61C65(L/LL)

TIMING CHARACTERISTICS

V_{DD} = 5 V ± 10%; T_{amb} = -40 to +85 °C; inputs levels = 0.4 to 2.4 V, input rise and fall times = 5 ns; input and output timing reference levels = 1.5 V and output loading as in Figure 3; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Read cycle					
t _{RC}	read cycle time		85	-	ns
t _{AA}	address access time		-	85	ns
t _{ACE}	chip enable access time		-	85	ns
t _{OE}	output enable access time		-	40	ns
t _{CLZ}	chip enable to output LOW Z	note 6	5	-	ns
t _{OLZ}	output enable to output LOW Z	note 6	5	-	ns
t _{CHZ}	chip disable to output HIGH Z	note 6	-	35	ns
t _{OHZ}	output disable to output HIGH Z	note 6	-	35	ns
t _{OH}	output hold time		10	-	ns
Write cycle					
t _{WC}	write cycle time		85	-	ns
t _{CW}	chip enable to end of write	note 11	70	-	ns
t _{AW}	address valid to end of write		70	-	ns
t _{AS}	address set-up time		0	-	ns
t _{WP}	write pulse width	note 9	40	-	ns
t _{WR}	write recovery time	note 10	5	-	ns
t _{WHZ}	write enable to output HIGH Z	note 16	-	35	ns
t _{DPW}	data to write time overlap		35	-	ns
t _{DPH}	data hold from write time		5	-	ns
t _{OW}	end of write to output LOW Z	note 16	5	-	ns

Output load



8 K x 8 Fast CMOS low-power static RAM for extended temperature range

FCF61C65(L/LL)

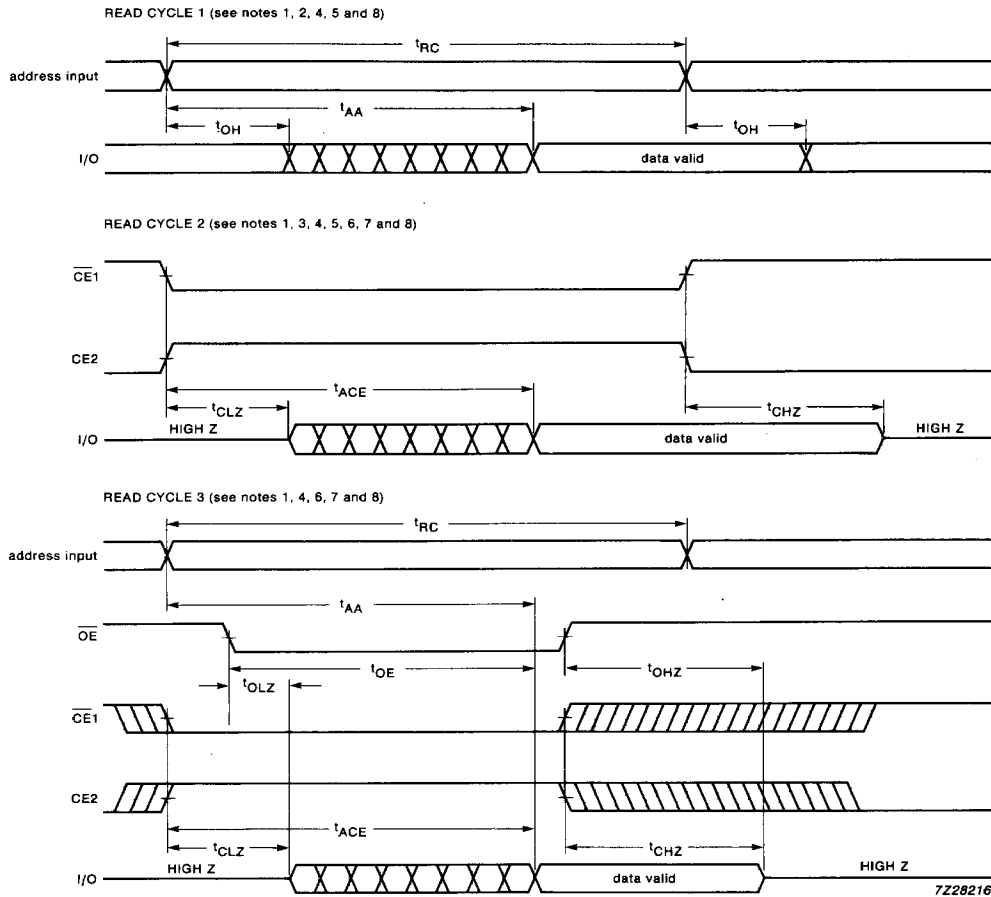
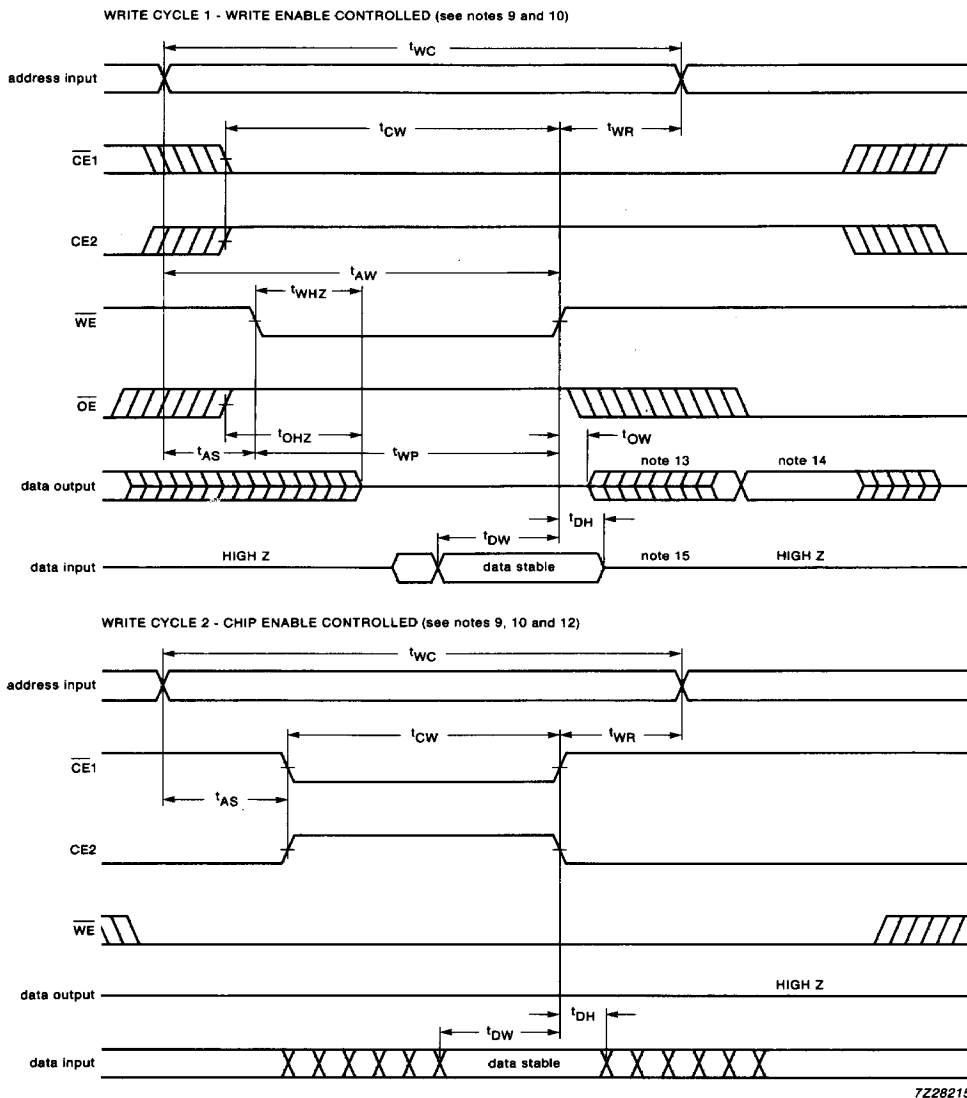


Fig.4 Read cycle timing.

8 K x 8 Fast CMOS low-power static RAM for extended temperature range

FCF61C65(L/LL)

Fig.5 Write cycle timing.

**8 K x 8 Fast CMOS low-power static RAM for
extended temperature range**

FCF61C65(L/LL)**Notes to the timing characteristics****Read cycle** (see Fig.4)

1. $\overline{WE}$ is HIGH for read cycle.
2. Device is continuously selected, $\overline{CE1}$ is LOW and CE2 is HIGH.
3. Address is valid prior to or coincident with $\overline{CE1}$ LOW or CE2 HIGH transition.
4. When $\overline{CE1}$ is LOW and CE2 HIGH, the address inputs may not be floating.
5. $\overline{OE}$ is LOW.
6. $C_L = 5$ pF for t_{CLZ} , t_{CHZ} , t_{OLZ} , output transition measured at ± 200 mV from preceding steady state. These parameters are sampled and not 100% tested.
7. t_{CLZ} and t_{ACE} are measured from the last $\overline{CE1}$ going LOW or CE2 going HIGH. t_{CHZ} is measured from the first of $\overline{CE1}$ going HIGH or CE2 going LOW.
8. If D OUT in two consecutive read cycles is the same, D OUT remains stable.

Write cycle (see Fig.5)

9. A write occurs during an overlap of LOW $\overline{CE1}$, a HIGH CE2 and a LOW $\overline{WE}$.
10. t_{WR} is measured from the earlier of CE2 going to LOW or $\overline{CE1}$ or $\overline{WE}$ going HIGH at the end of a write cycle.
11. If the $\overline{CE1}$ /CE2 transition occurs simultaneously to or after the $\overline{WE}$ LOW transition the outputs remain in a high impedance state.
12. $\overline{OE}$ is continuously LOW.
13. D OUT is in the same phase as the write data of this write cycle.
14. D OUT is the read data of the next address.
15. If $\overline{CE1}$ is LOW (CE2 is HIGH) and I/O pins are in the output state during this period then input data signals of opposite phase to the outputs must not be applied.
16. $C_L = 5$ pF for t_{WHZ} and t_{OW} , measured at ± 200 mV from steady state. These parameters are sampled and not 100% tested.

8 K x 8 Fast CMOS low-power static RAM for extended temperature range

FCF61C65(L/LL)

DATA RETENTION CHARACTERISTICS FOR LOW POWER/STANDBY MODE

(FCF61C65L/LL only)
 $T_{amb} = -40$ to $+85$ °C; I_{DRL} /LL measurements are valid after thermal equilibrium has been established.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Supply						
V_{DR}	supply voltage for data retention	$\overline{CE1} = \text{CMOSH}$ or $CE2 = \text{CMOSL}$ with other $V_I = \text{CMOS}$; note 1	2.0	-	5.5	V
I_{DRL} $I_{DRL\text{LL}}$	supply current during data retention FCF61C65L only FCF61C65LL only	$V_{DR} = 3$ V; $CE2 = \text{CMOSL}$; other $V_I = \text{CMOS}$ or $\overline{CE1} = \text{CMOSH}$; other $V_I = \text{CMOS}$ note 2 note 2	- -	2 0.05	100 4	μA μA
Timing						
t_{CDR}	chip disable to data retention time		0	-	-	ns
t_R	recovery time to fully active	note 3	t_{RC}	-	-	ns

Notes to the data retention characteristics

- CMOS = CMOSH: $V_{DR} - 0.2 \text{ V} \leq \text{level} \leq V_{DR} + 0.2 \text{ V}$ or
CMOSL: $-0.2 \text{ V} \leq \text{level} \leq +0.2 \text{ V}$.
- At $T_{amb} = 70$ °C: $I_{DRL} \leq 50 \mu\text{A}$ and $I_{DRL\text{LL}} \leq 1 \mu\text{A}$.
- t_{RC} = read cycle time.

